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Hyperfast Rectifier, 30 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES

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Models	App
	<u>IN</u>

PRIMARY CHARACTERISTICS						
I _{F(AV)}	30 A					
V _R	600 V					
V _F at I _F at 125 °C	1.3 V					
t _{rr} (typ.)	22					
I _{FSM}	310					
T _J max.	175 °C					
Package	TO-247AD 3L					
Circuit configuration	Single					

FEATURES

- Hyperfast and optimized Q_{rr}
- · Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- FREE • 175 °C maximum operating junction temperature
- Polyimide passivation
- AEC-Q101 qualified meets JESD 201 whisker test 2
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV on-board battery chargers

MECHANICAL DATA

Case: TO-247AD 3L

Molding compound meets UL 94 V-0 flammability rating Terminal: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 117 °C, D = 0.50	30				
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave both anodes, (1) and (3) connected	310	А			
Repetitive peak forward current	I _{FRM}	T _C = 117 °C, D = 0.50, f = 20 kHz	60				
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	600	-	-			
Forward voltage	VF	I _F = 30 A	-	1.6	2.1	V		
Forward voltage	۷F	I _F = 30 A, T _J = 125 °C	-	1.3	-			
Deverse leekees eurrent	1	V _R = V _R rated	-	-	20			
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	CT	V _R = 200 V	-	36	-	pF		
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH		

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 10$	00 A/µs, V _R = 30 V	-	22	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	39	-	ns	
		T _J = 125 °C		-	50	-		
Peak recovery current	1	T _J = 25 °C	I _F = 20 A dI _F /dt = 1000 A/μs V _R = 400 V	-	14	-	А	
Feak recovery current	I _{RRM}	T _J = 125 °C		-	24	-	A	
Powerse receivery charge	0	T _J = 25 °C		-	253	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	785	-		
	+	T _J = 25 °C		-	41	-		
Reverse recovery time	t _{rr}	T _J = 125 °C		-	56	-	ns	
Deels receiver a current		T _J = 25 °C	I _F = 30 A dI _F /dt = 1000 A/μs V _B = 400 V	-	16	-	А	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	27	-	А	
	0	T _J = 25 °C		-	306	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C	1	-	952	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.1	°C/W			
Weight			-	5.5	-	g			
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Marking device		Case style: TO-247AD 3L		A5PX3	006LH				

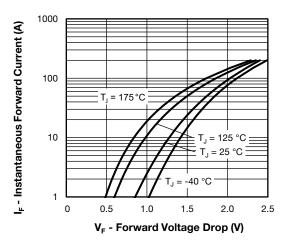


Fig. 1 - Typical Forward Voltage Drop Characteristics

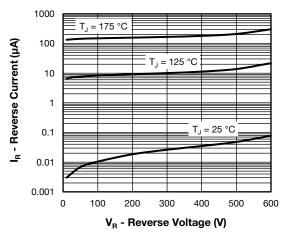
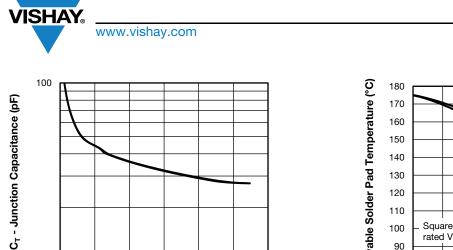


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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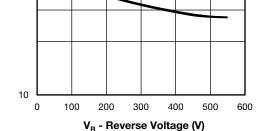
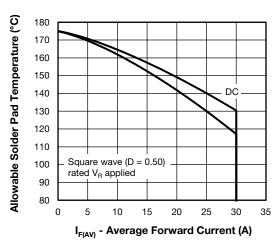


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



VS-A5PX3006LHN3

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Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

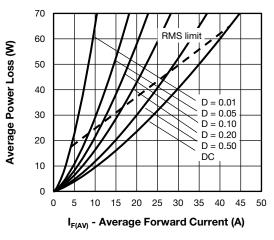


Fig. 5 - Average Power Loss vs. Average Forward Current

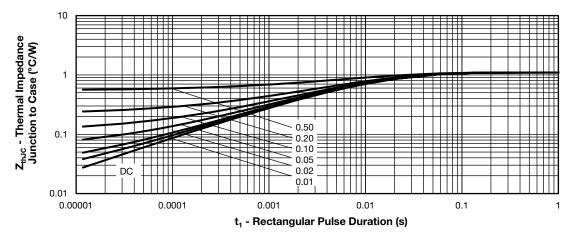


Fig. 6 - Thermal Impedance ZthJC - Characteristics



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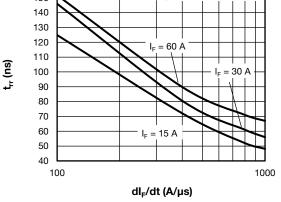


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

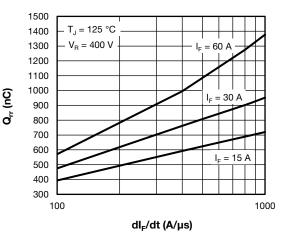


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

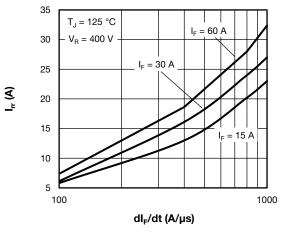


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

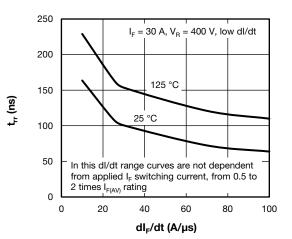


Fig. 10 - Typical Reverse Recovery Time vs. dI_F/dt

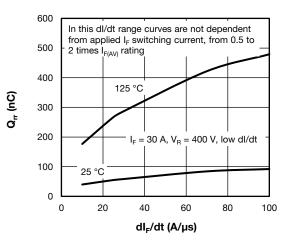


Fig. 11 - Typical Reverse Recovery Charge vs. dl_F/dt

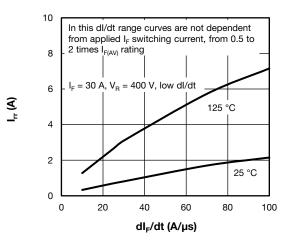


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt

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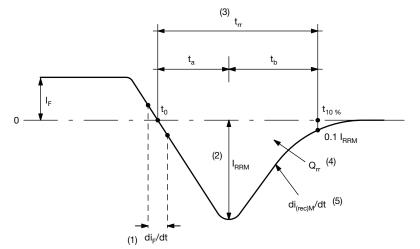


Fig. 13 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}$ di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM}
- $^{(4)}~Q_{rr}$ area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE

Device code	VS-	Α	5	Р	x	30	06	L	Н	N3
	1	2	3	4	5	6	7	8	9	10
	1 -	Visł	nay Sem	niconduo	ctors pro	oduct				
	2 -	- Circuit configuration								
	3 -		single o D Pt [®] (diode, 2	anodes					
	4 -			' packag	je					
	5 -		cess typ hyperfa	be: ast recov	/ery					
	6 -			ng (30 =	-					
	7 -	Volt	age rati	ng (06 =	= 600 V)					
	8 -	Pac	kage: L	= long	ead (TC)-247A[D)			
	9 -	H =	AEC-Q	101 qua	lified					
	10 -			ntal digit en-free,		complia	nt, and	totally l	ead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-A5PX3006LHN3	25	500	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95626				
Part marking information	www.vishay.com/doc?95007				

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TO-247AD 3L

DIMENSIONS in millimeters and inches



View B

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.34	0.065	0.092	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
с	0.38	0.89	0.015	0.035	
c1	0.38	0.84	0.015	0.033	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

(2, 52, 51) (4) Section C - C, D - D, E - E

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	-	
е	5.46	BSC	0.215	5 BSC	
ØК	0.2	254	0.0	010	
L	19.81	20.32	0.780	0.800	
L1	3.71	4.29	0.146	0.169	
ØР	3.56	3.66	0.14	0.144	
Ø P1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51	BSC	0.217	' BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

- ⁽³⁾ Dimension D and E do not include mold flash. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- ⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension A min., D, E min., Q min., S, and note 4

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